



60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D T _C = +25°C |
|-------------------|---------------------------------------|--|
| 60V | $10m\Omega$ @ V _{GS} = $10V$ | 89.5A |
| 607 | $12m\Omega$ @ $V_{GS} = 4.5V$ | 81.7A |

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. The device is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- High-Frequency switching
- Synchronous rectifications
- DC-DC converters

Features

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low RDS(ON)—Minimizes Power Losses
- Low Q_G—Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH6009LPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

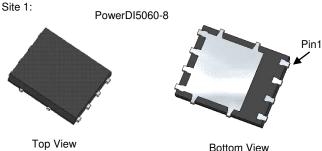
- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish—Matte Tin Annealed over Copper Leadframe, Solderable per MIL-STD-202, Method 208@3

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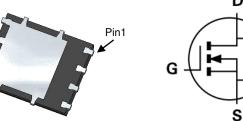
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Weight: 0.097 grams (Approximate)

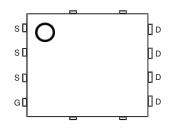


PowerDI5060-8/SWP (Type UX)

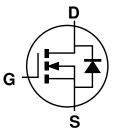
Site 2:



Internal Schematic



Top View Pin Configuration



Internal Schematic

Top View Pin Configuration

Ordering Information (Note 4)

Top View

| Part Number | Pankaga | Packing | | |
|-----------------|-----------------------------|---------|-------------|--|
| Part Number | Package | Qty. | Carrier | |
| DMTH6009LPSQ-13 | PowerDI5060-8 | 2500 | Tape & Reel | |
| DMTH6009LPSQ-13 | PowerDI5060-8/SWP (Type UX) | 2500 | Tape & Reel | |

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Bottom View

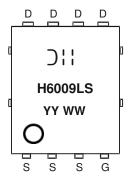
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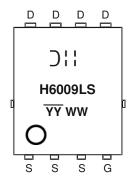
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Marking Information





) | | = Manufacturer's Code Marking H6009LS = Product Type Marking Code YYWW = Date Code Marking YY or YY = Year (ex: 23 = 2023) WW = Week (01 to 53)

Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit |
|--|---|------------------|--------------|------|
| Drain-Source Voltage | | V _{DSS} | 60 | V |
| Gate-Source Voltage | | Vgss | ±16 | V |
| Continuous Drain Current (Note 5) | $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$ | lο | 11.76 8.3 | А |
| Continuous Drain Current (Note 6) | T _C = +25°C T _C = +100°C | I _D | 89.5 63.3 | А |
| Maximum Continuous Body Diode Forward Current (Note 6) | | Is | 89 | Α |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | | Ірм | 350 | Α |
| Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%) | | Ism | 350 | Α |
| Avalanche Current, L = 0.1mH | | las | 20.3 | Α |
| Avalanche Energy, L = 0.1mH | | Eas | 20.6 | mJ |

Thermal Characteristics

| Characteristic | | Symbol | Value | Unit |
|--|------------------------|----------|-------------|------|
| Total Power Dissipation (Note 5) | T _A = +25°C | PD | 2.8 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | | Reja | 53 | °C/W |
| Total Power Dissipation (Note 6) | T _C = +25°C | PD | 136 | W |
| Thermal Resistance, Junction to Case (Note 6) | <u>.</u> | Rejc | 1.1 | °C/W |
| Operating and Storage Temperature Range | | TJ, TSTG | -55 to +175 | °C |

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

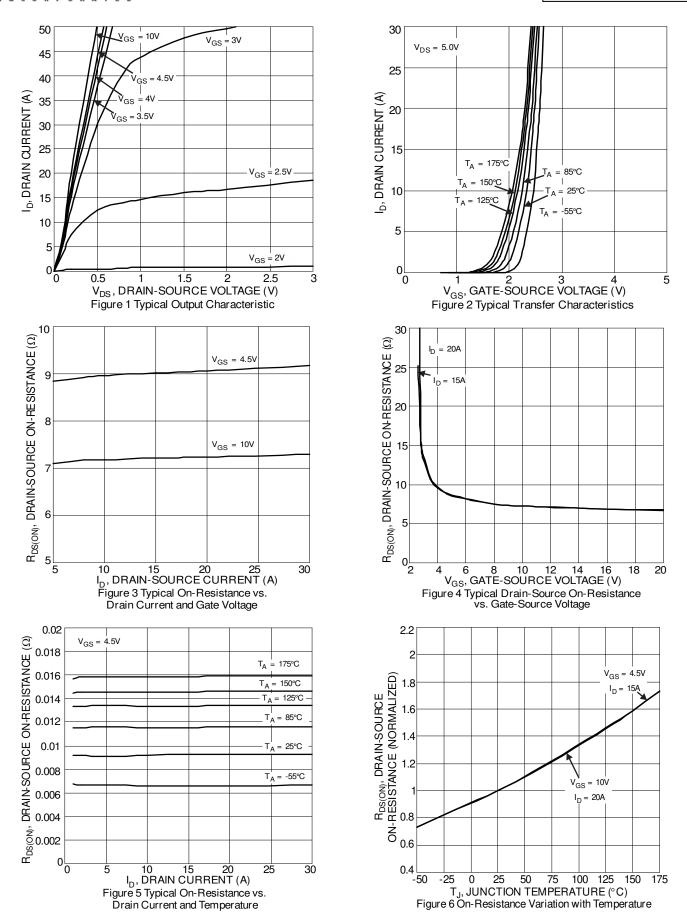
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|--|---------------------|-----|-------|------|-------|---|
| OFF CHARACTERISTICS (Note 7) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 60 | | _ | V | $V_{GS} = 0V$, $I_D = 1mA$ |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | 1 | μA | $V_{DS} = 48V$, $V_{GS} = 0V$ |
| Gate-Source Leakage | Igss | _ | _ | ±100 | nA | $V_{GS} = \pm 16V$, $V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 7) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 0.7 | _ | 2 | V | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ |
| Static Drain-Source On-Resistance | Descer | _ | 7.2 | 10 | mΩ | V _{GS} = 10V, I _D = 20A |
| Static Dialii-Source Off-Nesistance | RDS(ON) | _ | 8.9 | 12 | 11122 | $V_{GS} = 4.5V, I_D = 15A$ |
| Diode Forward Voltage | V _{SD} | _ | 0.9 | 1.2 | V | V _{GS} = 0V, I _S = 20A |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | |
| Input Capacitance | Ciss | _ | 1,925 | _ | | V 20V V 0V |
| Output Capacitance | Coss | _ | 438 | _ | pF | $V_{DS} = 30V$, $V_{GS} = 0V$, $f = 1MHz$ |
| Reverse Transfer Capacitance | Crss | _ | 41 | _ | | |
| Gate Resistance | Rg | _ | 1.7 | _ | Ω | $V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$ |
| Total Gate Charge (VGS = 10V) | Qg | _ | 33.5 | _ | | |
| Total Gate Charge (V _{GS} = 4.5V) | Qg | _ | 15.6 | _ | nC | V 20V I- 10 FA |
| Gate-Source Charge | Qgs | _ | 4.7 | _ | IIC | V _{DS} = 30V, I _D = 13.5A |
| Gate-Drain Charge | Qgd | _ | 5.3 | _ | | |
| Turn-On Delay Time | td(ON) | _ | 4.5 | _ | | |
| Turn-On Rise Time | t _R | _ | 8.6 | _ | | V _{DD} = 30V, V _{GS} = 10V, |
| Turn-Off Delay Time | tD(OFF) | _ | 35.9 | _ | ns | $R_G = 6\Omega$, $I_D = 13.5A$ |
| Turn-Off Fall Time | tF | _ | 15.7 | _ | | |
| Body Diode Reverse Recovery Time | trr | _ | 18.2 | _ | ns | I_ 10 5 A di/db 100 A /: |
| Body Diode Reverse Recovery Charge | Qrr | _ | 33.1 | _ | nC | F = 13.5A, di/dt = 400A/μs |

Notes:

^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.

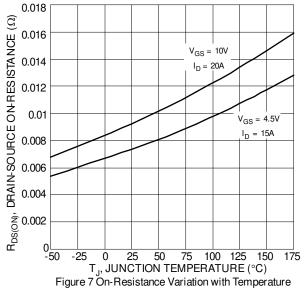


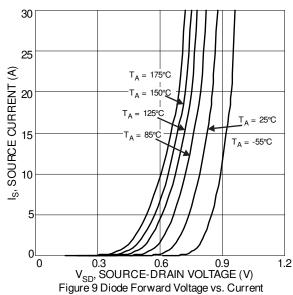


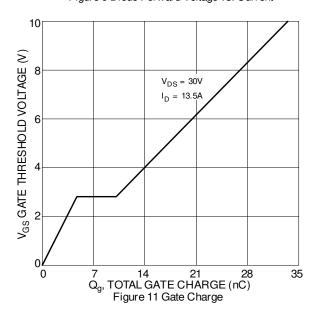


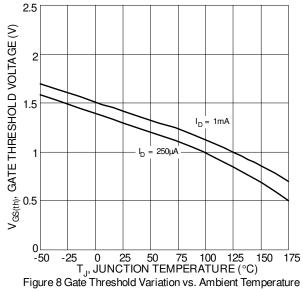


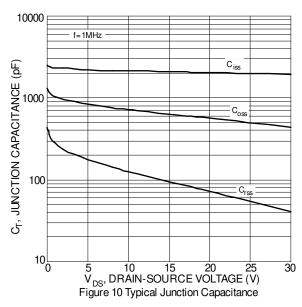


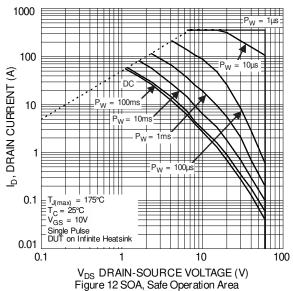




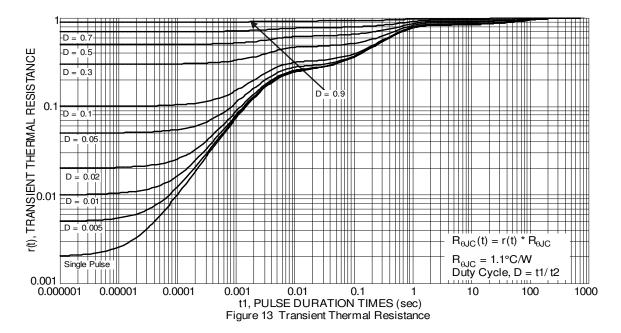










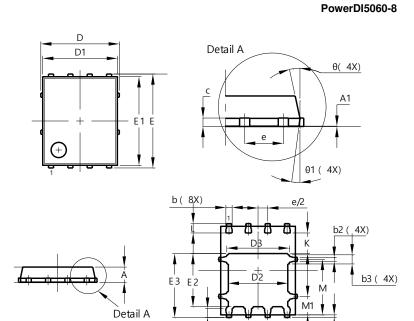




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

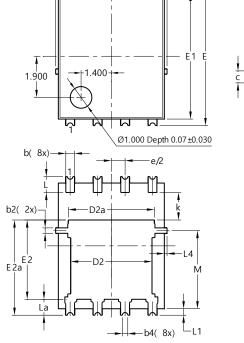
Site 1:



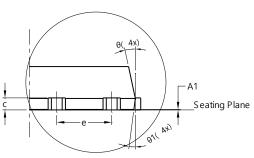
| D DIFFORD O | | | | |
|----------------------|-------|----------|-------|--|
| PowerDI5060-8 | | | | |
| Dim | Min | Max | Тур | |
| Α | 0.90 | 1.10 | 1.00 | |
| A 1 | 0.00 | 0.05 | _ | |
| b | 0.33 | 0.51 | 0.41 | |
| b2 | 0.200 | 0.350 | 0.273 | |
| b3 | 0.40 | 0.80 | 0.60 | |
| С | 0.230 | 0.330 | 0.277 | |
| D | ļ | 5.15 BSC | ; | |
| D1 | 4.70 | 5.10 | 4.90 | |
| D2 | 3.70 | 4.10 | 3.90 | |
| D3 | 3.90 | 4.30 | 4.10 | |
| Е | (| 6.15 BSC | ; | |
| E1 | 5.60 | 6.00 | 5.80 | |
| E2 | 3.28 | 3.68 | 3.48 | |
| E3 | 3.99 | 4.39 | 4.19 | |
| е | | 1.27 BSC | ; | |
| G | 0.51 | 0.71 | 0.61 | |
| K | 0.51 | - | _ | |
| L | 0.51 | 0.71 | 0.61 | |
| L1 | 0.100 | 0.200 | 0.175 | |
| М | 3.235 | 4.035 | 3.635 | |
| M1 | 1.00 | 1.40 | 1.21 | |
| Θ | 10° | 12° | 11° | |
| Θ1 | 6° | 8° | 7° | |
| All Dimensions in mm | | | | |

Site 2:

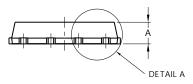
PowerDI5060-8/SWP (Type UX)



-D1



DETAIL A



| PowerDI5060-8/SWP | | | | |
|----------------------|----------|---------|-------|--|
| (Type UX) | | | | |
| Dim | Min | Max | Тур | |
| Α | 0.90 | 1.10 | 1.00 | |
| A 1 | 0 | 0.05 | | |
| b | 0.30 | 0.50 | 0.41 | |
| b2 | 0.20 | 0.35 | 0.25 | |
| b4 | C |).25REF | | |
| С | 0.230 | 0.330 | 0.277 | |
| D | | .15 BS(| 2 | |
| D1 | 4.70 | 5.10 | 4.90 | |
| D2 | 3.56 | 3.96 | 3.76 | |
| D2a | 3.78 | 4.18 | 3.98 | |
| E | | .40 BS0 |) | |
| E1 | 5.60 | 6.00 | 5.80 | |
| E2 | 3.46 | 3.86 | 3.66 | |
| E2a | 4.195 | 4.595 | 4.395 | |
| е | 1 | .27BSC |) | |
| k | 1.05 | | | |
| L | 0.635 | 0.835 | 0.735 | |
| La | 0.635 | 0.835 | 0.735 | |
| L1 | 0.200 | 0.400 | 0.300 | |
| L1a | 0.050REF | | | |
| L4 | 0.025 | 0.225 | 0.125 | |
| M | 3.205 | 4.005 | 3.605 | |
| θ | 10° | 12° | 11° | |
| θ1 | 6° | 8° | 7° | |
| All Dimensions in mm | | | | |

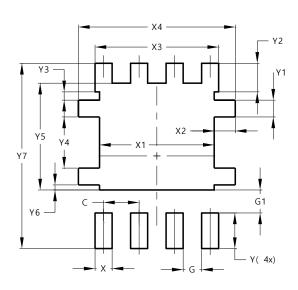


Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

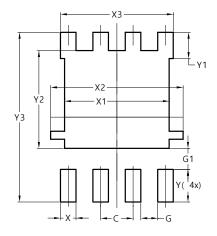
PowerDI5060-8



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 1.270 |
| G | 0.660 |
| G1 | 0.820 |
| X | 0.610 |
| X1 | 4.100 |
| X2 | 0.755 |
| Х3 | 4.420 |
| X4 | 5.610 |
| Υ | 1.270 |
| Y1 | 0.600 |
| Y2 | 1.020 |
| Y3 | 0.295 |
| Y4 | 1.825 |
| Y5 | 3.810 |
| Y6 | 0.180 |
| Y 7 | 6.610 |

Site 2:

PowerDI5060-8/SWP (Type UX)



| Dimensions | Value |
|--------------|---------|
| Difficusions | (in mm) |
| С | 1.270 |
| G | 0.660 |
| G1 | 0.820 |
| Х | 0.610 |
| X1 | 4.100 |
| X2 | 5.190 |
| Х3 | 4.420 |
| Υ | 1.270 |
| Y 1 | 1.020 |
| Y2 | 3.810 |
| Y3 | 6.610 |



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